

Description

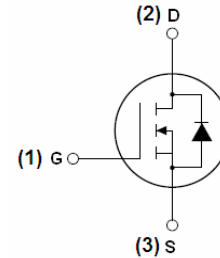
The SE1505S uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

General Features

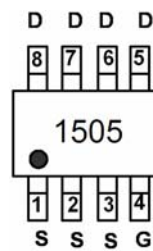
- $V_{DS} = 150V, I_D = 5.2A$
 $R_{DS(ON)} < 44m\Omega @ V_{GS}=10V$ (Typ: $31m\Omega$)
- High density cell design for ultra low R_{dson}
- Fully characterized avalanche voltage and current
- Low gate to drain charge to reduce switching losses

Application

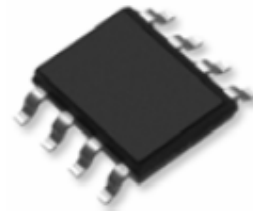
- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply



Schematic diagram



Marking and pin assignment



SOP-8 top view

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
1505	SE1505S	SOP-8	Ø330mm	12mm	4000 units

Absolute Maximum Ratings ($T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	150	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	5.2	A
Drain Current-Continuous($T_C=100^\circ C$)	$I_D(100^\circ C)$	3.7	A
Pulsed Drain Current(Note 1)	I_{DM}	42	A
Maximum Power Dissipation	P_D	3.5	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	$^\circ C$

Thermal Characteristic

Thermal Resistance, Junction-to-Case ^(Note 2)	$R_{\theta JC}$	35.7	$^\circ C/W$
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Electrical Characteristics ($T_A=25^\circ\text{C}$ unless otherwise noted)

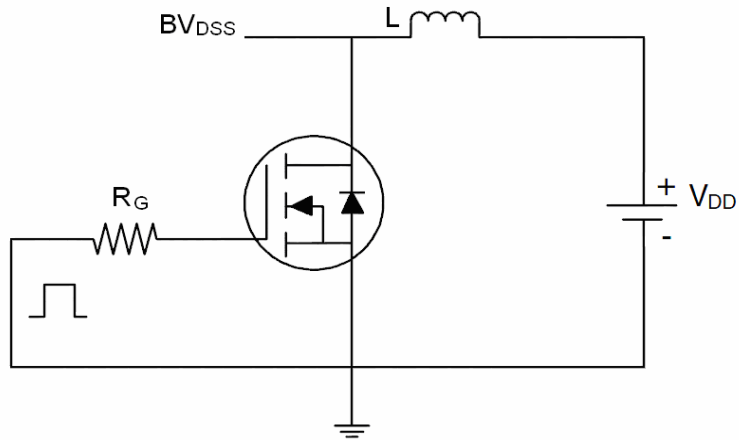
Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	150	170	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=150V, V_{GS}=0V$	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	2.5	3.2	4.5	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=5.2A$	-	31	44	m Ω
Forward Transconductance	g_{FS}	$V_{DS}=50V, I_D=5.2A$	12	-	-	S
Dynamic Characteristics (Note 4)						
Input Capacitance	C_{iss}	$V_{DS}=25V, V_{GS}=0V,$ $F=1.0MHz$	-	1700	-	PF
Output Capacitance	C_{oss}		-	190	-	PF
Reverse Transfer Capacitance	C_{rss}		-	90	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=75V, I_D=3.1A$ $V_{GS}=10V, R_{GEN}=6.5\Omega$	-	15	-	nS
Turn-on Rise Time	t_r		-	13	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	26	-	nS
Turn-Off Fall Time	t_f		-	14	-	nS
Total Gate Charge	Q_g	$V_{DS}=75V, I_D=3.1A,$ $V_{GS}=10V$	-	35.8	-	nC
Gate-Source Charge	Q_{gs}		-	7.5	-	nC
Gate-Drain Charge	Q_{gd}		-	13	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	$V_{GS}=0V, I_S=3.1A$	-	-	1.2	V
Diode Forward Current (Note 2)	I_S		-	-	2.7	A
Reverse Recovery Time	t_{rr}	$T_J = 25^\circ\text{C}, I_F = 3.1A,$ $di/dt = 100A/\mu s$	-	50	-	nS
Reverse Recovery Charge	Q_{rr}		-	140	-	nC

Notes:

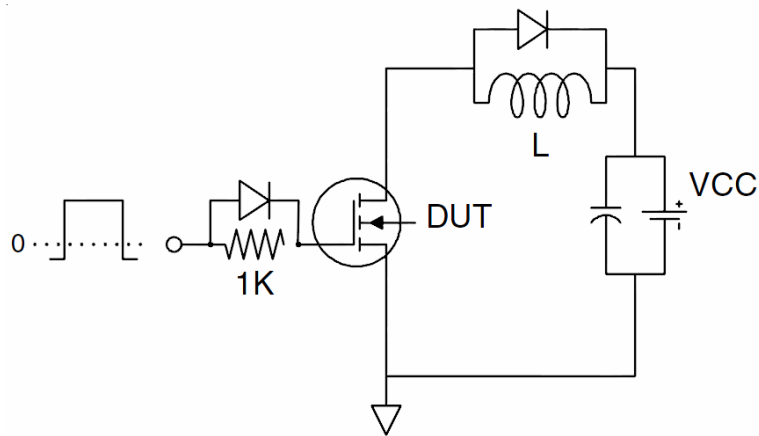
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production.

Test Circuit

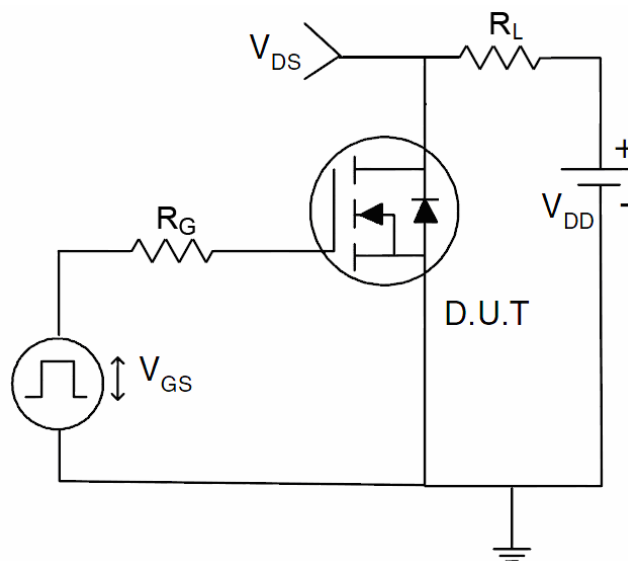
1) E_{AS} test Circuits



2) Gate charge test Circuit

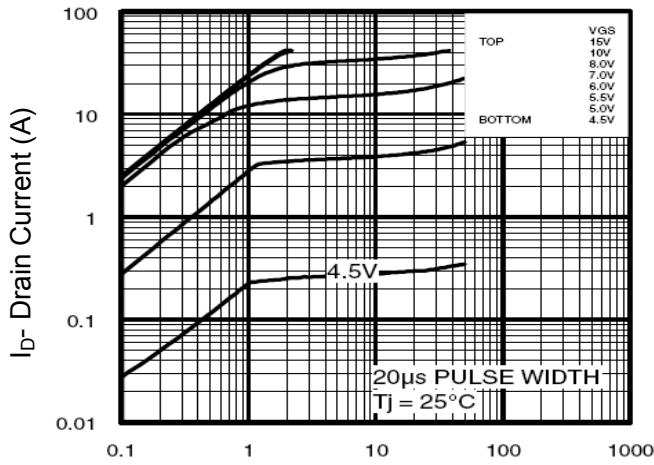


3) Switch Time Test Circuit

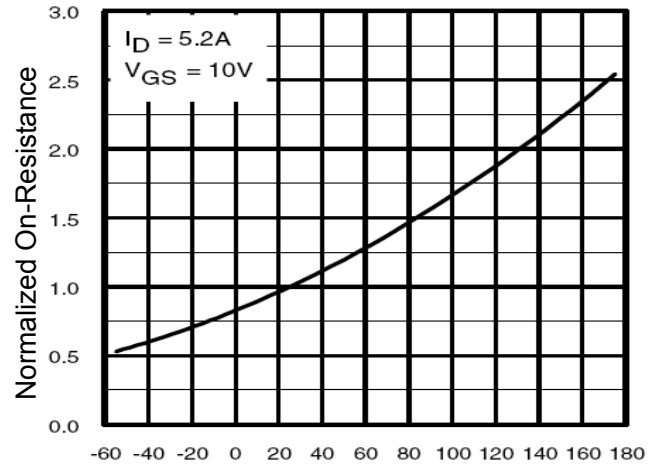




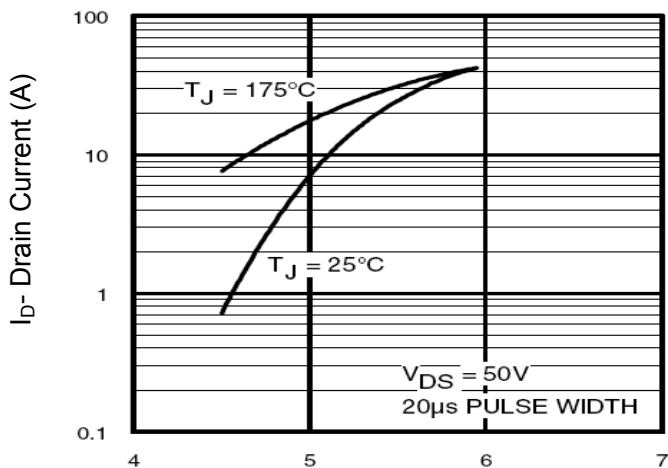
Typical Electrical and Thermal Characteristics (Curves)



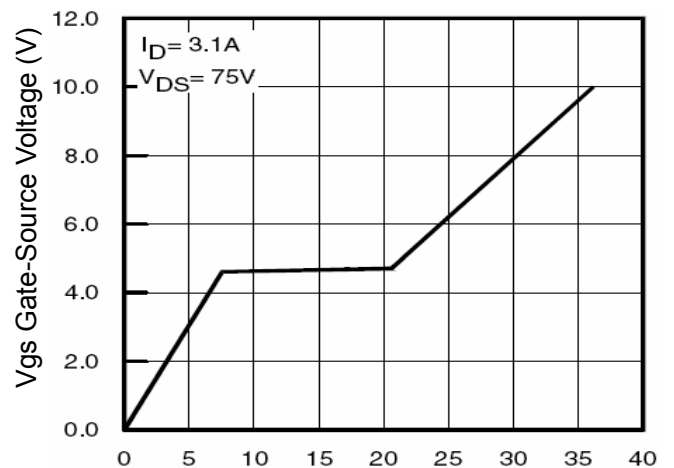
Vds Drain-Source Voltage (V)
Figure 1 Output Characteristics



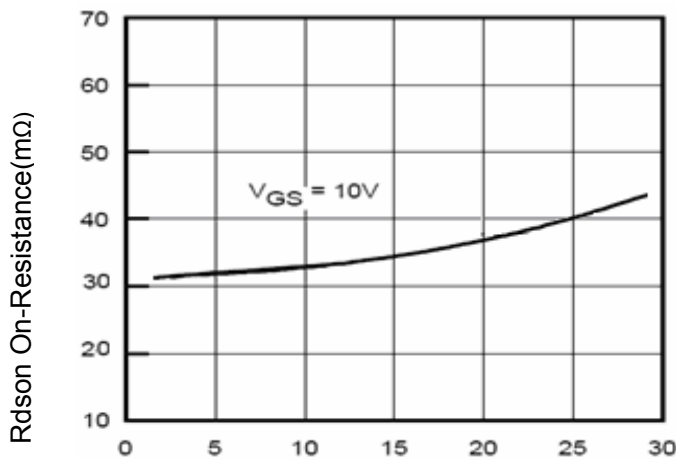
T_J-Junction Temperature(°C)
Figure 4 Rdson-Junction Temperature



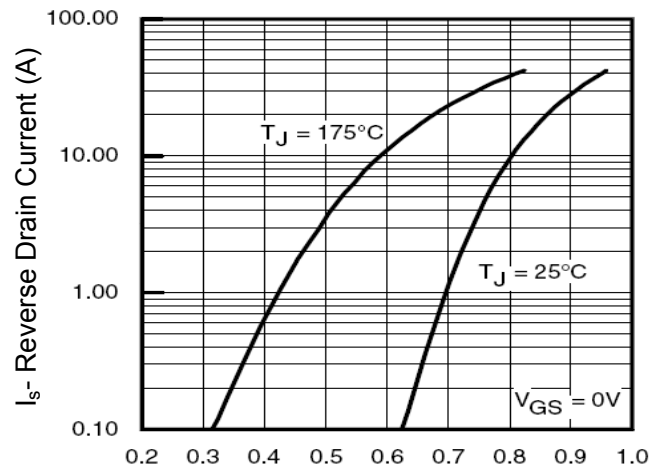
Vgs Gate-Source Voltage (V)
Figure 2 Transfer Characteristics



Qg Gate Charge (nC)
Figure 5 Gate Charge



Id- Drain Current (A)
Figure 3 Rdson- Drain Current



Vsd Source-Drain Voltage (V)
Figure 6 Source- Drain Diode Forward

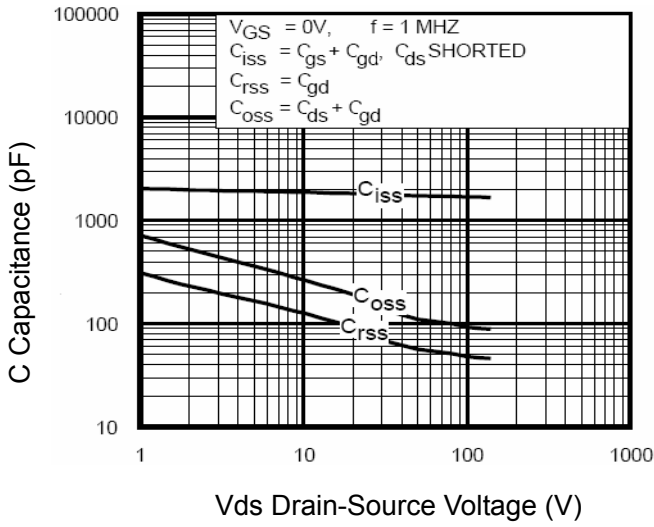


Figure 7 Capacitance vs Vds

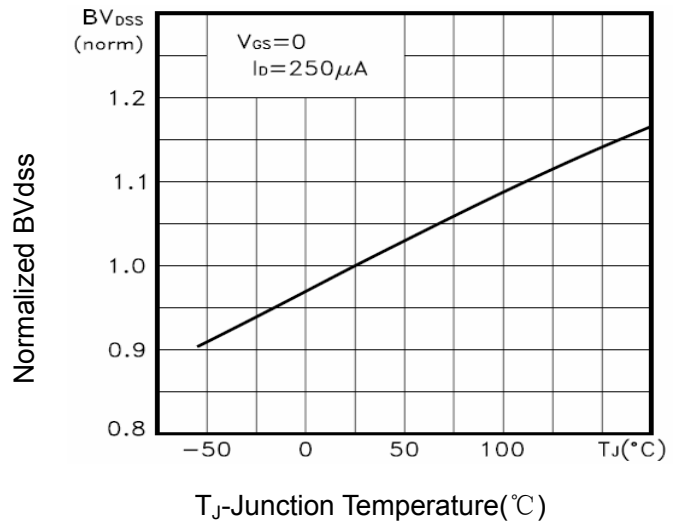


Figure 9 BV_{DSS} vs Junction Temperature

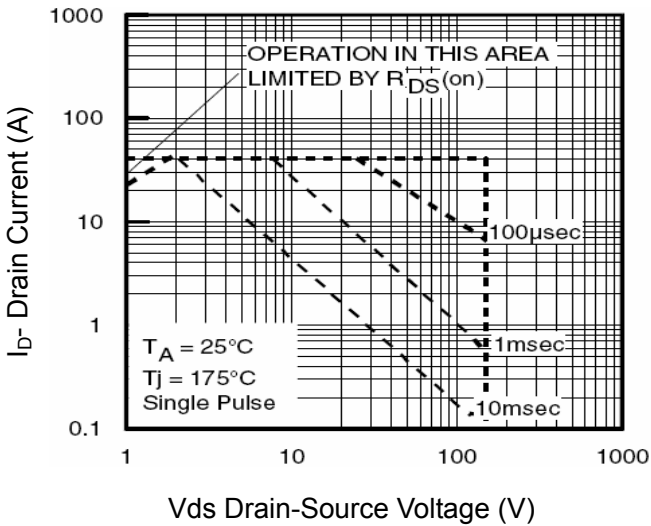


Figure 8 Safe Operation Area

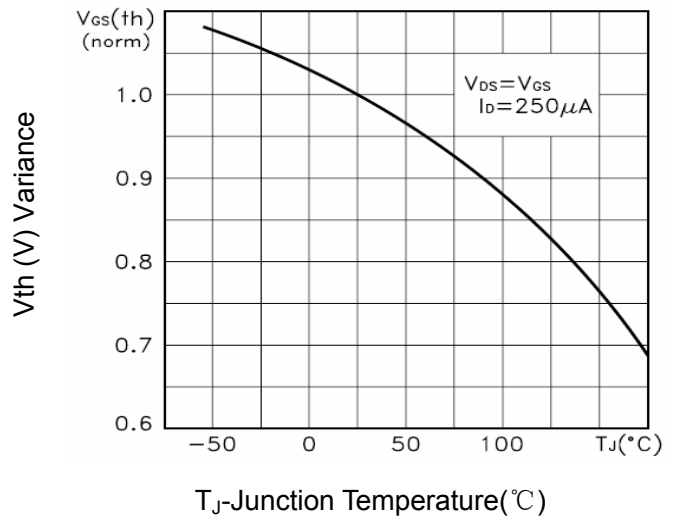


Figure 10 V_{GS(th)} vs Junction Temperature

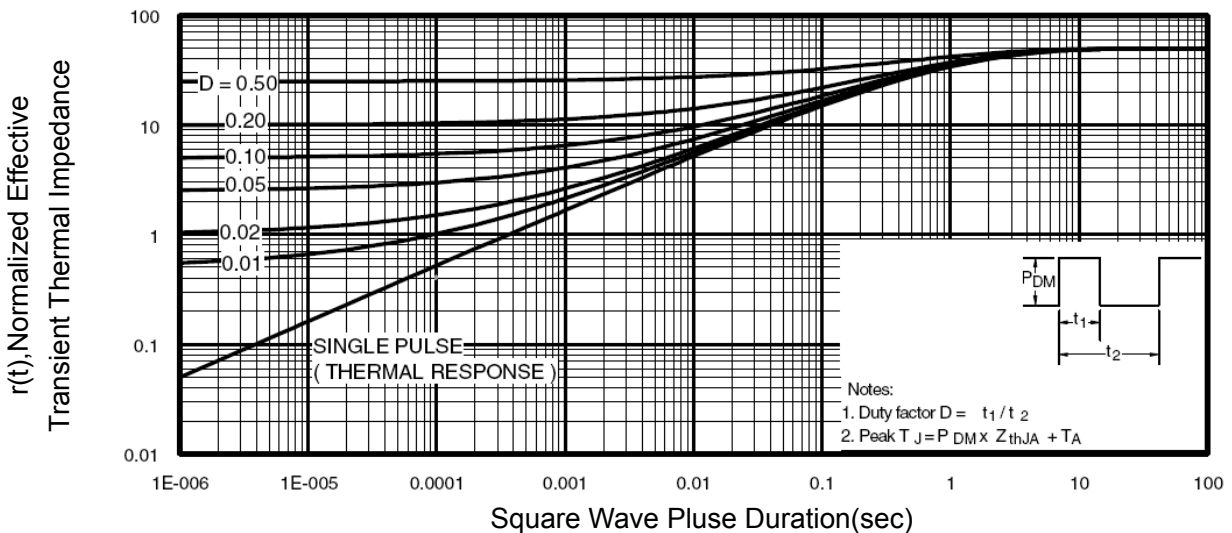
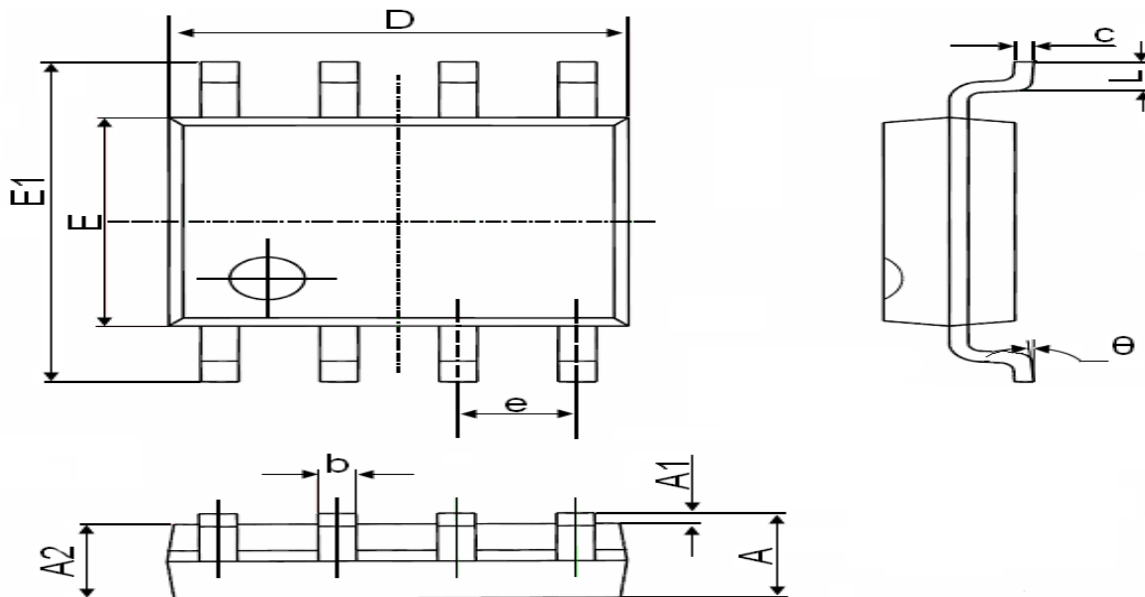


Figure 11 Normalized Maximum Transient Thermal Impedance

SOP-8 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270(BSC)		0.050(BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°